

Silicon NPN Power Transistors

2SC2774

DESCRIPTION

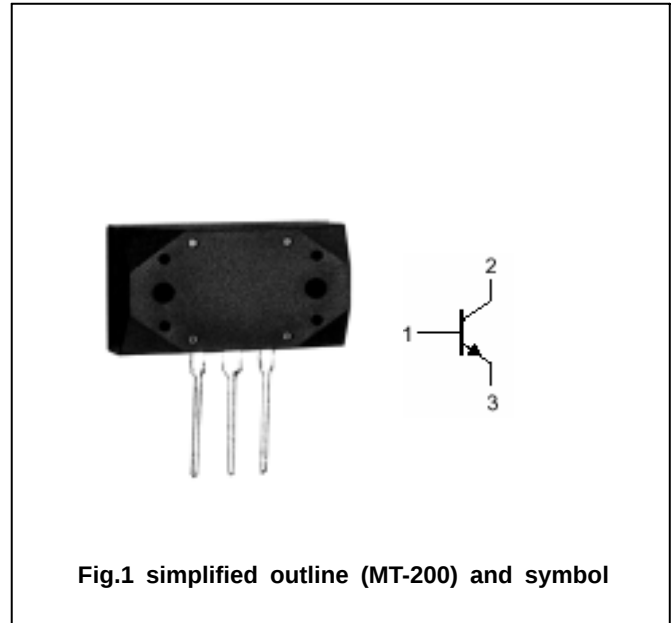
- With MT-200 package
- High power dissipation
- High current capability

APPLICATIONS

- For audio power amplifier and general purpose applications

PINNING(see Fig.2)

PIN	DESCRIPTION
1	Base
2	Collector;connected to mounting base
3	Emitter

Absolute maximum ratings($T_a=25^\circ\text{C}$)

SYMBOL	PARAMETER	CONDITIONS	VALUE	UNIT
V_{CBO}	Collector-base voltage	Open emitter	200	V
V_{CEO}	Collector-emitter voltage	Open base	200	V
V_{EBO}	Emitter-base voltage	Open collector	6	V
I_C	Collector current		17	A
I_B	Base current		5	A
P_C	Collector power dissipation	$T_C=25$	200	W
T_j	Junction temperature		150	
T_{stg}	Storage temperature		-55~150	

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2SC2774**CHARACTERISTICS****T_j=25** unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	TYP.	MAX	UNIT
$V_{(BR)CEO}$	Collector-emitter breakdown voltage	$I_C=25mA$; $I_B=0$	200			V
$V_{(BR)EBO}$	Emitter-base breakdown voltage	$I_E=1mA$; $I_C=0$	6			V
V_{CEsat}	Collector-emitter saturation voltage	$I_C=5A$; $I_B=0.5A$			2.0	V
I_{CBO}	Collector cut-off current	$V_{CB}=200V$; $I_E=0$			100	μA
I_{EBO}	Emitter cut-off current	$V_{EB}=5V$; $I_C=0$			100	μA
h_{FE}	DC current gain	$I_C=5A$; $V_{CE}=4V$	50		140	
C_{ob}	Output capacitance	$I_E=0$; $V_{CB}=10V$; $f=1MHz$		300		pF
f_T	Transition frequency	$I_C=2A$; $V_{CE}=12V$		20		MHz

◆ **h_{FE} classifications**

O	Y
50-100	70-140

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PACKAGE OUTLINE

